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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	400MHz
Co-Processors/DSP	Security; SEC 3.3
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	SATA 3Gbps (2)
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	620-BBGA Exposed Pad
Supplier Device Package	620-HBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=kmpc8315ecvragda

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



2.12 Power Management Controller (PMC)

The MPC8315E supports a range of power management states that significantly lower power consumption under the control of the power management controller. The PMC includes the following features:

- Provides power management when the device is used in both PCI host and agent modes
- PCI Power Management 1.2 D0, D1, D2, D3hot, and D3cold states
- PME generation in PCI agent mode, PME detection in PCI host mode
- Wake-up from Ethernet (magic packet), USB, GPIO, and PCI (PME input as host) while in the D1, D2 and D3hot states
- A new low-power standby power management state called D3warm
 - The PMC, one Ethernet port, and the GTM block remain powered via a split power supply controlled through an external power switch
 - Wake-up events include Ethernet (magic packet), GTM, GPIO, or IRQ inputs and cause the device to transition back to normal operation
 - PCI agent mode is not be supported in D3warm state
- PCI Express-based PME events are not supported

2.13 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) allows the MPC8315E to exchange data between other PowerQUICC family chips, Ethernet PHYs for configuration, and peripheral devices such as EEPROMs, real-time clocks, A/D converters, and ISDN devices.

The SPI is a full-duplex, synchronous, character-oriented channel that supports a four-wire interface (receive, transmit, clock, and slave select). The SPI block consists of transmitter and receiver sections, an independent baud-rate generator, and a control unit.

2.14 DMA Controller, I²C, DUART, Enhanced Local Bus Controller (eLBC), and Timers

The integrated four-channel DMA controller includes the following features:

- Allows chaining (both extended and direct) through local memory-mapped chain descriptors (accessible by local masters)
- Misaligned transfer capability for source/destination address
- Supports external DREQ, DACK and DONE signals

There is one I^2C controller. This synchronous, multi-master buses can be connected to additional devices for expansion and system development.

The DUART supports full-duplex operation and is compatible with the PC16450 and PC16550 programming models. 16-byte FIFOs are supported for both the transmitter and the receiver.

The eLBC port allows connections with a wide variety of external DSPs and ASICs. Three separate state machines share the same external pins and can be programmed separately to access different types of devices. The general-purpose chip select machine (GPCM) controls accesses to asynchronous devices



CAUTION

When the device is in D3 warm (standby) mode, all external voltage supplies applied to any I/O pins, with the exception of wake-up pins, must be turned off. Applying supplied external voltage to any I/O pins, except the wake up pins, while the device is in D3 warm standby mode may cause permanent damage to the device.

An example of the power-up sequence is shown in Figure 4 when implemented along with low power D3 warm mode.

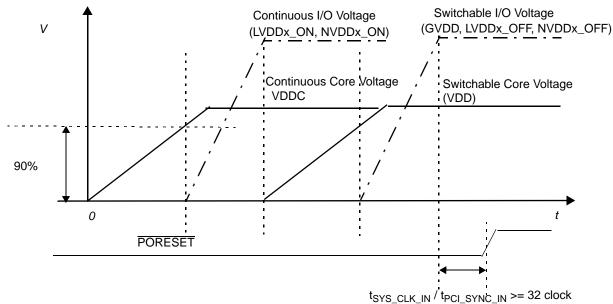


Figure 4. Power Up Sequencing Example with Low power D3 Warm Mode

The switchable and continuous supplies can be combined when the D3 warm mode is not used.

The SATA power supplies VDD33PLL and VDD33ANA should go high after NVDD3_OFF supply and go low before NVDD3_OFF supply. The NVDD3_OFF voltage levels should not drop below the VDD33PLL, VDD33ANA voltages at any time.



Clock Input Timing

5.1 DC Electrical Characteristics

This table provides the clock input (SYS_CLK_IN/PCI_SYNC_IN) DC timing specifications for the MPC8315E.

Parameter	Condition	Symbol	Min	Мах	Unit
Input high voltage	—	V _{IH}	2.4	NVDD + 0.3	V
Input low voltage	—	V _{IL}	-0.3	0.4	V
SYS_CLK_IN input current	$0 V \leq V_{IN} \leq NVDD$	I _{IN}	—	±10	μA
SYS_XTAL_IN input current	$0 V \leq V_{IN} \leq NVDD$	I _{IN}	—	±40	μA
PCI_SYNC_IN input current	$0 V \leq V_{IN} \leq NVDD$	I _{IN}	—	±10	μA
RTC_CLK input current	$0 V \leq V_{IN} \leq NVDD$	I _{IN}	—	±10	μA
USB_CLK_IN input current	$0 \text{ V} \leq \text{V}_{\text{IN}} \leq \text{NVDD}$	I _{IN}	—	±10	μA
USB_XTAL_IN input current	$0 V \leq V_{IN} \leq NVDD$	I _{IN}	—	±40	μA
SATA_CLK_IN input current	$0 \text{ V} \leq V_{IN} \leq NVDD$	I _{IN}	—	±10	μA

Table 6. SYS_CLK_IN DC Electrical Characteristics

5.2 AC Electrical Characteristics

The primary clock source for the MPC8315E can be one of two inputs, SYS_CLK_IN or PCI_CLK, depending on whether the device is configured in PCI host or PCI agent mode. This table provides the clock input (SYS_CLK_IN/PCI_CLK) AC timing specifications for the MPC8315E.

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Note
SYS_CLK_IN/PCI_CLK frequency	f _{SYS_CLK_IN}	24		66.67	MHz	1, 6, 7
SYS_CLK_IN/PCI_CLK cycle time	t _{SYS_CLK_IN}	15	—	41.6	ns	6
SYS_CLK_IN rise and fall time	t _{KH} , t _{KL}	0.6	—	4	ns	2, 6
PCI_CLK rise and fall time	t _{PCH} , t _{PCL}	0.6	0.8	1.2	ns	2
SYS_CLK_IN/PCI_CLK duty cycle	t _{KHK} /t _{SYS_CLK_IN}	40	—	60	%	3, 6
SYS_CLK_IN/PCI_CLK jitter	—	_	—	±150	ps	4, 5, 6

Table 7. SYS_CLK_IN AC Timing Specifications

Note:

- 1. **Caution:** The system, core, and security block must not exceed their respective maximum or minimum operating frequencies.
- 2. Rise and fall times for SYS_CLK_IN/PCI_CLK are specified at 20% to 80% of signal swing.
- 3. Timing is guaranteed by design and characterization.
- 4. This represents the total input jitter-short term and long term-and is guaranteed by design.
- 5. The SYS_CLK_IN/PCI_CLK driver's closed loop jitter bandwidth should be <500 kHz at -20 dB. The bandwidth must be set low to allow cascade-connected PLL-based devices to track SYS_CLK_IN drivers with the specified jitter.
- 6. The parameter names PCI_CLK and PCI_SYNC_IN are used interchangeably in this document.
- 7. Spread spectrum is allowed up to 1% down-spread at 33kHz.(max. rate).



DDR and DDR2 SDRAM

Table 14. DDR SDRAM Capacitance for GVDD(typ) = 2.5 V Interface

Delta input/output capacitance: DQ, DQS	C _{DIO}	 0.5	pF	1
Note:				

1. This parameter is sampled. GVDD = $2.5 \text{ V} \pm 0.125 \text{ V}$, f = 1 MHz, T_A = 25° C, V_{OUT} = GVDD/2, V_{OUT} (peak-to-peak) = 0.2 V.

This table provides the current draw characteristics for MV_{REF}.

Table 15. Current Draw Characteristics for MV_{REF}

Parameter / Condition	Symbol	Min	Max	Unit	Note
Current draw for MV _{REF}	I _{MVREF}	_	500	μΑ	1

Note:

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

7.2 DDR and DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR and DDR2 SDRAM interface.

7.2.1 DDR and DDR2 SDRAM Input AC Timing Specifications

This table lists the input AC timing specifications for the DDR2 SDRAM (GVDD(typ) = 1.8 V).

Table 16. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GVDD of $1.8V \pm 100 \text{ mV}$

Parameter	Symbol	Min	Мах	Unit	Note
AC input low voltage	V _{IL}	—	MVREF – 0.45	V	—
AC input high voltage	V _{IH}	MVREF + 0.45	_	V	—

This table lists the input AC timing specifications for the DDR SDRAM when GVDD(typ)=2.5 V.

Table 17. DDR SDRAM Input AC Timing Specifications for 2.5 V Interface

At recommended operating conditions with GVDD of $2.5V \pm 200 \text{ mV}$

Parameter	Symbol Min		Мах	Unit	Note
AC input low voltage	V _{IL}	—	MVREF – 0.51	V	
AC input high voltage	V _{IH}	MVREF + 0.51		V	

The following two tables list the input AC timing specifications for the DDR SDRAM interface.

Table 18. DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GVDD of (1.8 V± 100 mV)

Parameter	Symbol	Min	Max	Unit	Note
Controller Skew for MDQS—MDQ 266 MHz 200 MHz		875 1250	875 1250	ps	1, 2, 3



DDR and DDR2 SDRAM

7.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions

Parameter	Symbol ¹	Min	Мах	Unit	Note
MCK[n] cycle time at MCK[n]/MCK[n] crossing	t _{MCK}	7.5	10	ns	2
ADDR/CMD output setup with respect to MCK 266 MHz 200 MHz		2.9 3.5	_	ns	3
ADDR/CMD output hold with respect to MCK 266 MHz 200 MHz		3.15 4.20	_	ns	3
MCS[n] output setup with respect to MCK 266 MHz 200 MHz		3.15 4.20	_	ns	3
MCS[n] output hold with respect to MCK 266 MHz 200 MHz		3.15 4.20	_	ns	3
MCK to MDQS Skew	t _{DDKHMH}	-0.6	0.6	ns	4
MDQ//MDM output setup with respect to MDQS 266 MHz 200 MHz	DDRLDS	900 1000	_	ps	5
MDQ//MDM output hold with respect to MDQS 266 MHz 200 MHz	DDRLDA	1100 1200		ps	5
MDQS preamble start	t _{DDKHMP}	$-0.5\times t_{MCK}-0.6$	$-0.5\times t_{MCK} + 0.6$	ns	6
MDQS epilogue end	t _{DDKHME}	-0.6	0.6	ns	6

Note:

- The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
 </sub>
- 2. All MCK/MCK referenced measurements are made from the crossing of the two signals ±0.1 V.
- 3. ADDR/CMD includes all DDR SDRAM output signals except MCK/MCK, MCS, and MDQ//MDM/MDQS.
- 4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This is typically set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the MPC8315E PowerQUICC II Pro Integrated Host Processor Family Reference Manual for a description and understanding of the timing modifications enabled by use of these bits.
- 5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
- 6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.



Table 28. RMII Receive AC Timing Specifications (continued)

At recommended operating conditions with LVDD of 3.3 V \pm 300 mv

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK	t _{RMRDVKH}	4.0	_	_	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK	t _{RMRDXKH}	2.0	_	_	ns
REF_CLK clock rise V _{IL} (min) to V _{IH} (max)	t _{RMXR}	1.0	_	4.0	ns
REF_CLK clock fall time $V_{IH}(max)$ to $V_{IL}(min)$	t _{RMXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of t_{(first three letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{RMRDVKH} symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, t_{RMRDXKL} symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{RMX} clock reference (K) going to the high (H) state or setup time. Also, t_{RMRDXKL} symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) went invalid (X) relative to the t_{RMX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{RMX} represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}

This figure provides the AC test load.

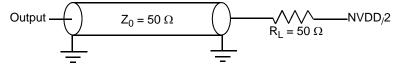


Figure 14. AC Test Load

This figure shows the RMII receive AC timing diagram.

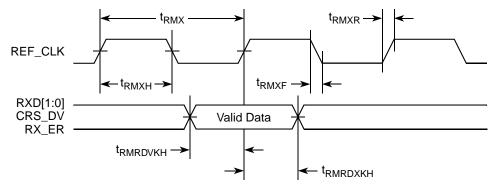


Figure 15. RMII Receive AC Timing Diagram

9.2.3 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

Table 29. RGMII and RTBI AC Timing Specifications

At recommended operating conditions (see Table 2)

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
Data to clock output skew (at transmitter)	t _{SKRGT}	-0.6	_	0.6	ns
Data to clock input skew (at receiver) ²	t _{SKRGT}	1.0		2.6	ns



Ethernet: Three-Speed Ethernet, MII Management

Table 30. MII Management DC Electrical Characteristics Powered at 3.3 V (continued)

Parameter	Symbol	Conditions		Min	Max	Unit
Input low current	۱ _{IL}	NVDD = Max	$V_{IN} = 0.5 V$	-600	_	μA

Note:

1. The symbol V_{IN} , in this case, represents the NV_{IN} symbol referenced in Table 1 and Table 2.

9.3.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 31. MII Management AC Timing Specifications

At recommended operating conditions with NVDD is 3.3 V ± 300 mv

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit	Note
MDC frequency	f _{MDC}	—	2.5	—	MHz	2
MDC period	t _{MDC}	—	400	—	ns	—
MDC clock pulse width high	t _{MDCH}	32	—	—	ns	—
MDC to MDIO delay	t _{MDKHDX}	10	—	170	ns	3
MDIO to MDC setup time	t _{MDDVKH}	5	—	—	ns	—
MDIO to MDC hold time	t _{MDDXKH}	0	—	—	ns	—
MDC rise time	t _{MDCR}	—	—	10	ns	—
MDC fall time	t _{MDHF}	—		10	ns	—

Note:

The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

2. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 133 MHz, the maximum frequency is 4.16 MHz and the minimum frequency is 0.593 MHz).

3. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 133 MHz, the delay is 60 ns).

Ethernet: Three-Speed Ethernet, MII Management

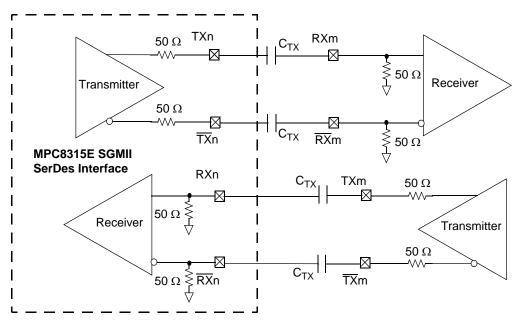


Figure 18. 4-Wire AC-Coupled SGMII Serial Link Connection Example

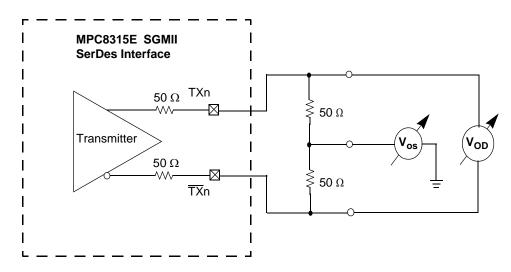


Figure 19. SGMII Transmitter DC Measurement Circuit

Table 36	. SGMII DC	Receiver	Electrical	Characteristics
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Parameter		Symbol	Min	Тур	Max	Unit	Note
Supply Voltage		XCOREVDD	0.95	1.0	1.05	V	—
DC Input voltage range		—		N/A		—	1
Input differential voltage	EQ = 0	V _{RX_DIFFp-p}	100	—	1200	mV	2, 4
	EQ = 1		175	—			
Loss of signal threshold	EQ = 0	VLOS	30	—	100	mV	3, 4
	EQ = 1		65	—	175		



12.2 JTAG AC Timing Specifications

This section describes the AC electrical specifications for the IEEE 1149.1 (JTAG) interface. This table provides the JTAG AC timing specifications as defined in Figure 29 through Figure 32.

Table 46. JTAG AC Timing Specifications (Independent of SYS_CLK_IN)¹

At recommended operating conditions (see Table 2)

Parameter	Symbol ²	Min	Max	Unit	Note
JTAG external clock frequency of operation	f _{JTG}	0	33.3	MHz	—
JTAG external clock cycle time	t _{JTG}	30	—	ns	—
JTAG external clock pulse width measured at 1.4 V	t _{JTKHKL}	15	—	ns	—
JTAG external clock rise and fall times	t _{JTGR} , t _{JTGF}	0	2	ns	—
TRST assert time	t _{TRST}	25	—	ns	3
Input setup times: Boundary-scan data TMS, TDI	t _{JTDVKH} tJTIVKH	4 4		ns	4
Input hold times: Boundary-scan data TMS, TDI	t _{JTDXKH} t _{JTIXKH}	10 10	_	ns	4
Valid times: Boundary-scan data TDO	t _{JTKLDV} t _{JTKLOV}	2 2	11 11	ns	5
Output hold times: Boundary-scan data TDO	t _{JTKLDX} t _{JTKLOX}	2 2		ns	5
JTAG external clock to output high impedance: Boundary-scan data TDO	t _{jtkldz} t _{jtkloz}	2 2	19 9	ns	5, 6

Note:

 All outputs are measured from the midpoint voltage of the falling/rising edge of t_{TCLK} to the midpoint of the signal in question. The output timings are measured at the pins. All output timings assume a purely resistive 50-Ω load (see Table 28). Time-of-flight delays must be added for trace lengths, vias, and connectors in the system.

- 2. The symbols used for timing specifications herein follow the pattern of t_{(first two letters of functional block)(signal)(state) (reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{JTDVKH} symbolizes JTAG device timing (JT) with respect to the time data input signals (D) reaching the valid state (V) relative to the t_{JTG} clock reference (K) going to the high (H) state or setup time. Also, t_{JTDXKH} symbolizes JTAG timing (JT) with respect to the time data input signals (D) went invalid (X) relative to the t_{JTG} clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}
- 3. TRST is an asynchronous level sensitive signal. The setup time is for test purposes only.
- 4. Non-JTAG signal input timing with respect to t_{TCLK}.
- 5. Non-JTAG signal output timing with respect to t_{TCLK}.
- 6. Guaranteed by design and characterization.



This figure shows the AC timing diagram for the I^2C bus.

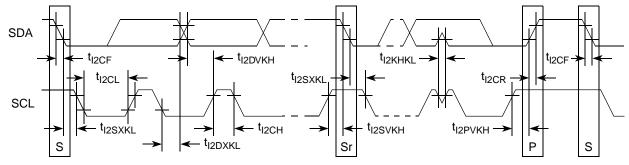


Figure 34. I²C Bus AC Timing Diagram

14 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8315E.

14.1 PCI DC Electrical Characteristics

This table provides the DC electrical characteristics for the PCI interface.

Parameter	Symbol	Test Condition	Min	Мах	Unit
High-level input voltage	V _{IH}	$V_{OUT} \ge V_{OH}$ (min) or	0.5 x NVDD	NVDD + 0.3	V
Low-level input voltage	V _{IL}	$V_{OUT} \le V_{OL}$ (max)	-0.5	0.3 imes NVDD	V
High-level output voltage	V _{OH}	NVDD = min, I _{OH} = -500 μA	0.9 x NVDD	—	V
Low-level output voltage	V _{OL}	NVDD = min, I _{OL} = 1500 μΑ	—	0.1 x NVDD	V
Input current	I _{IN}	$0 \text{ V} \leq \text{V}_{\text{IN}} \leq \text{NVDD}$	—	± 10	μA

Table 49. PCI DC Electrical Characteristics ¹

Note:

1. The symbol V_{IN} , in this case, represents the NV_{IN} symbol referenced in Table 1 and Table 2.

14.2 PCI AC Electrical Specifications

This section describes the general AC timing parameters of the PCI bus. Note that the PCI_CLK or PCI_SYNC_IN signal is used as the PCI input clock depending on whether the MPC8315E is configured as a host or agent device. This table shows the PCI AC timing specifications at 66 MHz.

Parameter	Symbol ¹	Min	Мах	Unit	Note
Clock to output valid	t _{PCKHOV}	—	6.0	ns	2
Output hold from clock	t _{PCKHOX}	1	—	ns	2
Clock to output high impedance	t _{PCKHOZ}	—	14	ns	2, 3
Input setup to clock	t _{PCIVKH}	3.3	_	ns	2, 4

 Table 50. PCI AC Timing Specifications at 66 MHz



PCI Express

Parameter	Symbol	Comments	Min	Typical	Max	Unit	Note
De-Emphasized differential output voltage (ratio)	V _{TX-DE-RATIO}	Ratio of the $V_{TX-DIFFp-p}$ of the second and following bits after a transition divided by the $V_{TX-DIFFp-p}$ of the first bit after a transition.	-3.0	-3.5	-4.0	dB	2
Minimum TX eye width	T _{TX-EYE}	The maximum Transmitter jitter can be derived as $T_{TX-MAX-JITTER} = 1 - U_{TX-EYE} = 0.3$ UI.	0.70	—	_	UI	2, 3
Maximum time between the jitter median and maximum deviation from the median	T _{TX-EYE-MEDIAN-to-} MAX-JITTER	Jitter is defined as the measurement variation of the crossing points $(V_{TX-DIFFp-p} = 0 V)$ in relation to a recovered TX UI. A recovered TX UI is calculated over 3500 consecutive unit intervals of sample data. Jitter is measured using all edges of the 250 consecutive UI in the center of the 3500 UI used for calculating the TX UI.		_	0.15	UI	2, 3
D+/D- TX output rise/fall time	T _{TX-RISE} , T _{TX-FALL}	—	0.125	—	—	UI	2, 5
RMS AC peak common mode output voltage	V _{TX-CM-ACp}		_	—	20	mV	2
Absolute delta of DC common mode voltage during L0 and electrical idle	V _{TX-CM-DC-} ACTIVE- IDLE-DELTA	$\label{eq:loss} \begin{array}{l} V_{TX}\text{-CM-DC} (\text{during L0}) - V_{TX}\text{-CM-Idle-DC} \\ (\text{During Electrical Idle}) <= 100 \text{ mV} \\ V_{TX}\text{-CM-DC} = \text{DC}_{(\text{avg})} \text{ of } V_{TX}\text{-D} + V_{TX}\text{-D} /2 \\ [\text{L0}] \\ V_{TX}\text{-CM-Idle-DC} = \text{DC}_{(\text{avg})} \text{ of } V_{TX}\text{-D} + \\ V_{TX}\text{-D} /2 \end{tabular} \begin{array}{l} \text{Electrical Idle} \\ \text{Electrical Idle} \end{array}$	0	_	100	mV	2
Absolute delta of DC common mode between D+ and D–	V _{TX-CM-DC} -LINE-DELTA	$\begin{split} V_{\text{TX-CM-DC-D+}} - V_{\text{TX-CM-DC-D-}} &<= 25 \text{ mV} \\ V_{\text{TX-CM-DC-D+}} = DC_{(\text{avg})} \text{ of } V_{\text{TX-D+}} \\ V_{\text{TX-CM-DC-D-}} = DC_{(\text{avg})} \text{ of } V_{\text{TX-D-}} \end{split}$	0	—	25	mV	2
Electrical idle differential peak output voltage	V _{TX-IDLE} -DIFFp	$V_{TX-IDLE-DIFFp} = V_{TX-IDLE-D+} - V_{TX-IDLE-D-} $ <= 20 mV	0	—	20	mV	2
Amount of voltage change allowed during receiver detection	V _{TX-RCV} -DETECT	The total amount of voltage change that a transmitter can apply to sense whether a low impedance Receiver is present.	—	—	600	mV	6
TX DC common mode voltage	V _{TX-DC-CM}	The allowed DC Common Mode voltage under any conditions.		—	3.6	V	6
TX short circuit current limit	I _{TX-SHORT}	The total current the Transmitter can provide when shorted to its ground	_	—	90	mA	_
Minimum time spent in electrical idle	T _{TX-IDLE-MIN}	Minimum time a Transmitter must be in Electrical Idle Utilized by the Receiver to start looking for an Electrical Idle Exit after successfully receiving an Electrical Idle ordered set	50	_		UI	_



21.1 SPI DC Electrical Characteristics

This table provides the DC electrical characteristics for the SPI.

Table 66. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V _{IH}	—	2.1	NVDD + 0.3	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	—	_	±5	μA
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

21.2 SPI AC Timing Specifications

This table and provide the SPI input and output AC timing specifications.

Table 67.	SPI AC	Timing	Specifications ¹
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Characteristic	Symbol ²	Min	Max	Unit
SPI outputs valid—master mode (internal clock) delay	t _{NIKHOV}	_	6	ns
SPI outputs hold—master mode (internal clock) delay	t _{NIKHOX}	0.5		ns
SPI outputs valid—slave mode (external clock) delay	t _{NEKHOV}	_	8.5	ns
SPI outputs hold—slave mode (external clock) delay	t _{NEKHOX}	2	—	ns
SPI inputs—master mode (internal clock) input setup time	t _{NIIVKH}	6	—	ns
SPI inputs—master mode (internal clock)input hold time	t _{NIIXKH}	0	—	ns
SPI inputs—slave mode (external clock) input setup time	t _{NEIVKH}	4	—	ns
SPI inputs—slave mode (external clock) input hold time	t _{NEIXKH}	2	—	ns

Note:

1. Output specifications are measured from the 50% level of the rising edge of SPICLK to the 50% level of the signal. Timings are measured at the pin.

The symbols used for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{NIKHOX} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load for the SPI.

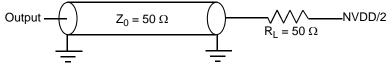
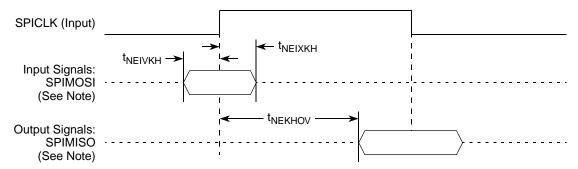


Figure 56. SPI AC Test Load

Figure 57 and Figure 58 represent the AC timing from Table 67. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.



This figure shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.



This figure shows the SPI timing in master mode (internal clock).

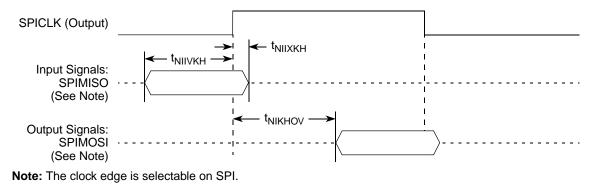


Figure 58. SPI AC Timing in Master Mode (Internal Clock) Diagram

22 TDM

This section describes the DC and AC electrical specifications for the TDM of the MPC8315E.

22.1 TDM DC Electrical Characteristics

This table provides the DC electrical characteristics TDM.

 Table 68. TDM DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V
Input high voltage	V _{IH}	—	2.1	NVDD + 0.3	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	$0 \text{ V} \leq \text{V}_{IN} \leq \text{NVDD}$		± 5	μA



Table 70. MPC8315E TEPBGA II Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Note
	DDR Memory Controller Interface	9		
MEMC_MDQ[0]	AF16	I/O	GVDD	
MEMC_MDQ[1]	AE17	I/O	GVDD	
MEMC_MDQ[2]	AH17	I/O	GVDD	
MEMC_MDQ[3]	AG17	I/O	GVDD	
MEMC_MDQ[4]	AG18	I/O	GVDD	
MEMC_MDQ[5] AH18		I/O	GVDD	
MEMC_MDQ[6] AD18		I/O	GVDD	
MEMC_MDQ[7]	AF19	I/O	GVDD	
MEMC_MDQ[8]	AH19	I/O	GVDD	
MEMC_MDQ[9]	AD19	I/O	GVDD	
MEMC_MDQ[10]	AG20	I/O	GVDD	
MEMC_MDQ[11]	AH20	I/O	GVDD	
MEMC_MDQ[12]	AH21	I/O	GVDD	
MEMC_MDQ[13]	AE21	I/O	GVDD	
MEMC_MDQ[14]	AH22	I/O	GVDD	
MEMC_MDQ[15]	AD21	I/O	GVDD	
MEMC_MDQ[16]	AG10	I/O	GVDD	
MEMC_MDQ[17]	AH9	I/O	GVDD	
MEMC_MDQ[18]	AH8	I/O	GVDD	
MEMC_MDQ[19]	AD11	I/O	GVDD	
MEMC_MDQ[20]	AH7	I/O	GVDD	
MEMC_MDQ[21]	AG7	I/O	GVDD	
MEMC_MDQ[22]	AF8	I/O	GVDD	
MEMC_MDQ[23]	AD10	I/O	GVDD	
MEMC_MDQ[24]	AE9	I/O	GVDD	
MEMC_MDQ[25]	AH6	I/O	GVDD	—
MEMC_MDQ[26]	AH5	I/O	GVDD	
MEMC_MDQ[27]	AG6	I/O	GVDD	
MEMC_MDQ[28]	AH4	I/O	GVDD	—
MEMC_MDQ[29]	AE6	I/O	GVDD	—
MEMC_MDQ[30]	AD8	I/O	GVDD	—
MEMC_MDQ[31]	AF5	I/O	GVDD	—
MEMC_MDM0	AE18	0	GVDD	—
MEMC_MDM1	AE20	0	GVDD	—
MEMC_MDM2	AE10	0	GVDD	—



Signal	Package Pin Number	Pin Type	Power Supply	Note
	Local Bus Controller Interface			
LAD0	AB28	I/O	NVDD3_OFF	11
LAD1	AB27	I/O	NVDD3_OFF	11
LAD2	AC28	I/O	NVDD3_OFF	11
LAD3	AA24	I/O	NVDD3_OFF	11
LAD4	AC27	I/O	NVDD3_OFF	11
LAD5	AD28	I/O	NVDD3_OFF	11
LAD6	AB25	I/O	NVDD3_OFF	11
LAD7	AC26	I/O	NVDD3_OFF	11
LAD8	AD27	I/O	NVDD3_OFF	11
LAD9	AB24	I/O	NVDD3_OFF	11
LAD10	AE28	I/O	NVDD3_OFF	11
LAD11	AE27	I/O	NVDD3_OFF	11
LAD12	AE26	I/O	NVDD3_OFF	11
LAD13	AF28	I/O	NVDD3_OFF	11
LAD14	AC24	I/O	NVDD3_OFF	11
LAD15	AD25	I/O	NVDD3_OFF	11
LA16	V24	0	NVDD3_OFF	11
LA17	V25	0	NVDD3_OFF	11
LA18	W26	0	NVDD3_OFF	11
LA19	W28	0	NVDD3_OFF	11
LA20	U24	0	NVDD3_OFF	11
LA21	W24	0	NVDD3_OFF	11
LA22	Y28	0	NVDD3_OFF	11
LA23	AH23	0	NVDD3_OFF	11
LA24	AH24	0	NVDD3_OFF	11
LA25	AG23	0	NVDD3_OFF	11
LCS[0]	AD22	0	NVDD3_OFF	12
LCS[1]	AF25	0	NVDD3_OFF	12
LCS[2]	AG24	0	NVDD3_OFF	12
LCS[3]	AF24	0	NVDD3_OFF	12
LWE[0] /LFWE/LBS	AE23	0	NVDD3_OFF	12
LWE[1]	AG26	0	NVDD3_OFF	12
LBCTL	AH26	0	NVDD3_OFF	12
LALE	AF26	0	NVDD3_OFF	11
LGPL0/LFCLE	Y27	0	NVDD3_OFF	_



Signal	Package Pin Number	Pin Type	Power Supply	Note
PCI_AD[9]	F28	I/O	NVDD2_OFF	
PCI_AD[10]	G25	I/O	NVDD2_OFF	—
PCI_AD[11]	F27	I/O	NVDD2_OFF	
PCI_AD[12]	E27	I/O	NVDD2_OFF	
PCI_AD[13]	E28	I/O	NVDD2_OFF	
PCI_AD[14]	D28	I/O	NVDD2_OFF	
PCI_AD[15]	D27	I/O	NVDD2_OFF	
PCI_AD[16]	B25	I/O	NVDD2_OFF	
PCI_AD[17]	D24	I/O	NVDD2_OFF	
PCI_AD[18]	B26	I/O	NVDD2_OFF	
PCI_AD[19]	C24	I/O	NVDD2_OFF	
PCI_AD[20]	A26	I/O	NVDD2_OFF	
PCI_AD[21]	E20	I/O	NVDD2_OFF	_
PCI_AD[22]	A23	I/O	NVDD2_OFF	—
PCI_AD[23]	C22	I/O	NVDD2_OFF	_
PCI_AD[24]	E19	I/O	NVDD2_OFF	_
PCI_AD[25]	A22	I/O	NVDD2_OFF	—
PCI_AD[26]	C20	I/O	NVDD2_OFF	_
PCI_AD[27]	B21	I/O	NVDD2_OFF	_
PCI_AD[28]	D19	I/O	NVDD2_OFF	_
PCI_AD[29]	A19	I/O	NVDD2_OFF	<u> </u>
PCI_AD[30]	A21	I/O	NVDD2_OFF	_
PCI_AD[31]	B19	I/O	NVDD2_OFF	_
PCI_C/BE[0]	H24	I/O	NVDD2_OFF	_
PCI_C/BE[1]	C27	I/O	NVDD2_OFF	_
PCI_C/BE[2]	A25	I/O	NVDD2_OFF	_
PCI_C/BE[3]	E21	I/O	NVDD2_OFF	_
PCI_PAR	G24	I/O	NVDD2_OFF	_
PCI_FRAME	C28	I/O	NVDD2_OFF	5
PCI_TRDY	A24	I/O	NVDD2_OFF	5
PCI_IRDY	D25	I/O	NVDD2_OFF	5
PCI_STOP	D23	I/O	NVDD2_OFF	5
PCI_DEVSEL	E22	I/O	NVDD2_OFF	5
PCI_IDSEL	D26	I	NVDD2_OFF	1 -
PCI_SERR	C25	I/O	NVDD2_OFF	5
PCI_PERR	D21	I/O	NVDD2_OFF	5

Table 70. MPC8315E TEPBGA II Pinout Listing (continued)



Table 70. MPC8315E TEPBGA II Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note
	ETSEC2			
GPIO_26/TSEC2_COL	A8	I/O	LVDD2_ON	_
GPIO_27/TSEC2_CRS	E9	I/O	LVDD2_ON	_
TSEC2_GTX_CLK	B10	0	LVDD2_ON	_
TSEC2_RX_CLK	B8	I	LVDD2_ON	_
TSCE2_RX_DV	C9	I	LVDD2_ON	_
TSEC2_RXD[3]	C10	I	LVDD2_ON	-
TSEC2_RXD[2]	D10	I	LVDD2_ON	_
TSEC2_RXD[1]	A9	I	LVDD2_ON	-
TSEC2_RXD[0]	B9	I	LVDD2_ON	-
TSEC2_RX_ER	A10	I	LVDD2_ON	_
TSEC2_TX_CLK	D8	I	LVDD2_ON	-
TSEC2_TXD[3]/CFG_RESET_SOURCE[0]	D11	I/O	LVDD2_ON	—
TSEC2_TXD[2]/CFG_RESET_SOURCE[1]	C7	I/O	LVDD2_ON	_
TSEC2_TXD[1]/CFG_RESET_SOURCE[2]	E8	I/O	LVDD2_ON	_
TSEC2_TXD[0]/CFG_RESET_SOURCE[3]	B7	I/O	LVDD2_ON	_
TSEC2_TX_EN	D12	0	LVDD2_ON	_
TSEC2_TX_ER	B11	0	LVDD2_ON	_
	SGMII / PCI Express PHY			
ТХА	P4	0	XPADVDD	_
TXA	N4	0	XPADVDD	_
RXA	R1	I	XCOREVDD	_
RXA	P1	I	XCOREVDD	
ТХВ	U4	0	XPADVDD	-
TXB	V4	0	XPADVDD	-
RXB	U1	I	XCOREVDD	-
RXB	V1	I	XCOREVDD	-
SD_IMP_CAL_RX	N3	I	XCOREVDD	-
SD_REF_CLK	R4	I	XCOREVDD	_
SD_REF_CLK	R5	I	XCOREVDD	-
SD_PLL_TPD	T2	0	_	—
SD_IMP_CAL_TX	V5	I	XPADVDD	—
SDAVDD	Т3	I	_	—
SD_PLL_TPA_ANA	T4	0	_	—
SDAVSS	T5	I	_	—
	USB Phy	· ·		



RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110–1111	Reserved

Table 73. System PLL Multiplication Factors	Table 73. S	vstem PLL	. Multiplication	Factors
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As described in Section 24, "Clocking," The LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_SYS_CLKIN_DIV configuration input signal select the ratio between the primary clock input (SYS_CLK_IN or PCI_CLK) and the internal coherent system bus clock (*csb_clk*). Table 74 and Table 75 shows the expected frequency values for the CSB frequency for select *csb_clk* to SYS_CLK_IN/PCI_SYNC_IN ratios.

Table 74. CSB Frequency Options for Host Mode

CFG_SYS_CLKIN_DIV at Reset ¹	SPMF	csb_clk : Input Clock	Input Clock Frequency (MHz) ²		
al Nesel		Ratio ²	24	33.33	66.67
High/Low ³	0010	2:1			133
High/Low	0011	3:1		100	_
High/Low	0100	4:1	96	133	—
High/Low	0101	5:1	120		—

¹ CFG_SYS_CLKIN_DIV select the ratio between SYS_CLK_IN and PCI_SYNC_OUT.

² SYS_CLK_IN is the input clock in host mode; PCI_CLK is the input clock in agent mode.

³ In the Host mode it does not matter if the value is High or Low.

Table 75. C	SB Frequency	Options for	Agent Mode
-------------	--------------	-------------	------------

CFG_SYS_CLKIN_DIV at Reset ¹	SPMF	IF csb_clk : Input Clock IF Ratio ² 25 23 23		Input Clock frequency (Mi	
arneser		Ratio ²	25	33.33	66.67
High	0010	2: 1			133
High	0011	3: 1		100	_
High	0100	4: 1		133	_
High	0101	5: 1	120		

¹ CFG_SYS_CLKIN_DIV doubles csb_clk if set low.

² SYS_CLK_IN is the input clock in host mode; PCI_CLK is the input clock in agent mode.



System Design Information

Power and ground connections must be made to all external VDD, GVDD, LVDD, NVDD, and GND pins of the device.

26.5 Output Buffer DC Impedance

The MPC8315E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to NVDD or GND. Then, the value of each resistor is varied until the pad voltage is NVDD/2 (see Figure 64). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals NVDD/2. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N)/2$.

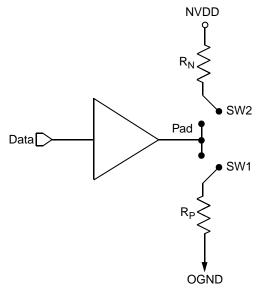


Figure 64. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.

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